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TRANSISTORS, HIGH POWER, PNP

BASED ON TYPE 2N5153

ESCC Detail Specification No. 5204/002

| | |
|---------|--------------|
| Issue 9 | October 2020 |
|---------|--------------|



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| DCR No. | CHANGE DESCRIPTION |
|---------|---|
| 1365 | Specification updated to incorporate changes per DCR. |

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1 GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. [5000](#)
- (b) [MIL-STD-750](#), Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. [21300](#) shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 520400201R

- Detail Specification Reference: 5204002
- Component Type Variant Number: 01 (as required)
- Total Dose Radiation Level Letter: R (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

| Variant Number | Based on Type | Case | Lead/Terminal Material and Finish | Weight max g | Total Dose Radiation Level Letter |
|----------------|---------------|--------|-----------------------------------|--------------|-----------------------------------|
| 01 | 2N5153 | TO-39 | D2 | 1.5 | R [100kRAD(Si)] |
| 02 | 2N5153 | TO-39 | D3 or D4 | 1.5 | R [100kRAD(Si)] |
| 03 | 2N5153 | TO-39 | D7 | 1.5 | R [100kRAD(Si)] |
| 04 | 2N5153 | TO-257 | H2 | 5 | R [100kRAD(Si)] |
| 05 | 2N5153 | TO-257 | H4 | 5 | R [100kRAD(Si)] |
| 06 | 2N5153 | SMD.5 | Q14 | 2 | R [100kRAD(Si)] |
| 07 | 2N5153 | SMD.5 | Q14 | 2 | R [100kRAD(Si)] |
| 08 | 2N5153 | Die | N/A | N/A | R [100kRAD(Si)] |

The lead/terminal material and finish shall be in accordance with the requirements of ESCC Basic Specification No. [23500](#).

Total dose radiation level letters are defined in ESCC Basic Specification No. [22900](#). If an alternative radiation test level is specified in the Purchase Order, the letter shall be changed accordingly.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

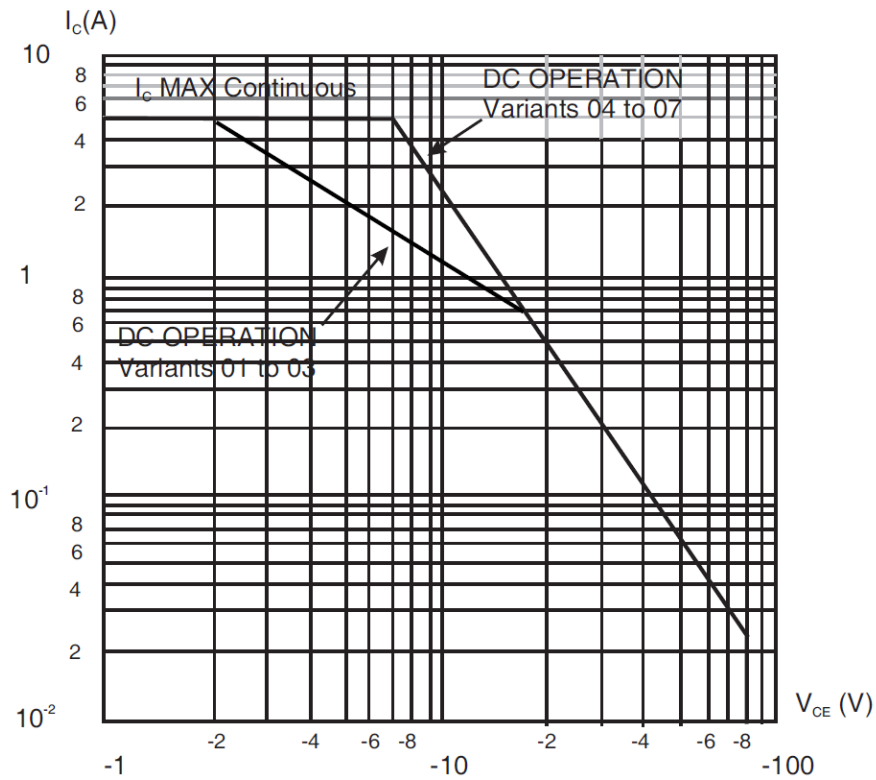
Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

| Characteristics | Symbols | Maximum Ratings | Unit | Remarks |
|---|---------------|-----------------|---------------|---|
| Collector-Base Voltage | V_{CB0} | -100 | V | Over T_{op} |
| Collector-Emitter Voltage | V_{CEO} | -80 | V | Over T_{op} Note 5 |
| Emitter-Base Voltage | V_{EBO} | -5.5 | V | Over T_{op} |
| Collector Current | I_c | -5 | A | Continuous Note 5 |
| Power Dissipation For TO-39 For TO-257 and SMD.5 | P_{tot1} | 1 3.3 | W | At $T_{amb} \leq +25^{\circ}C$ Note 1 |
| | P_{tot2} | 10 35 | W | At $T_{case} \leq +25^{\circ}C$ Note 1 |
| Thermal Resistance, Junction-to-Ambient For TO-39 For TO-257 and SMD.5 | $R_{th(j-a)}$ | 175 | $^{\circ}C/W$ | |
| | | 53 | | |
| Thermal Resistance, Junction-to-Case For TO-39 For TO-257 and SMD.5 | $R_{th(j-c)}$ | 17.5 | $^{\circ}C/W$ | |
| | | 5 | | |
| Operating Temperature Range | T_{op} | -65 to +200 | $^{\circ}C$ | Note 2 |
| Storage Temperature Range | T_{stg} | -65 to +200 | $^{\circ}C$ | Note 2 |
| Soldering Temperature For TO-39 and TO-257 For SMD.5 | T_{sol} | +260 | $^{\circ}C$ | Note 3 |
| | | +245 | | Note 4 |

NOTES:

- For T_{amb} or $T_{case} > +25^{\circ}C$, derate linearly to 0W at +200°C.
- For Variants with tin-lead plating or hot solder dip lead finish all testing, and any handling, performed at $T_{amb} > +125^{\circ}C$ shall be carried out in a 100% inert atmosphere.
- Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
- Duration 5 seconds maximum and the same package shall not be resoldered until 3 minutes have elapsed.
- Safe Operating Area applies as follows:

Maximum Safe Operating Area Graph

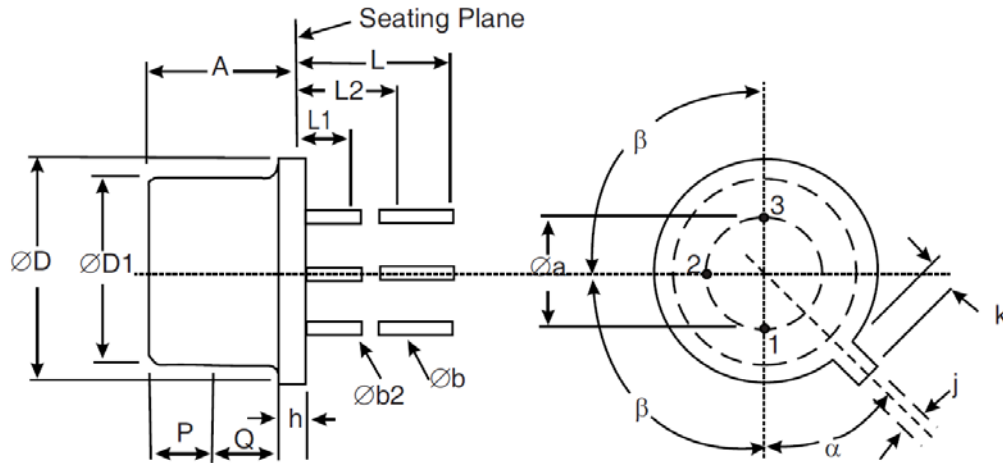


1.6 HANDLING PRECAUTIONS

The TO-257 package contains Beryllium Oxide (BeO) and therefore it must not be ground, machined, sandblasted or subjected to any mechanical operation which will produce dust. The case must not be subjected to any chemical process (e.g. etching) which will produce fumes.

1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.7.1 Metal Can Package (TO-39) - 3 lead



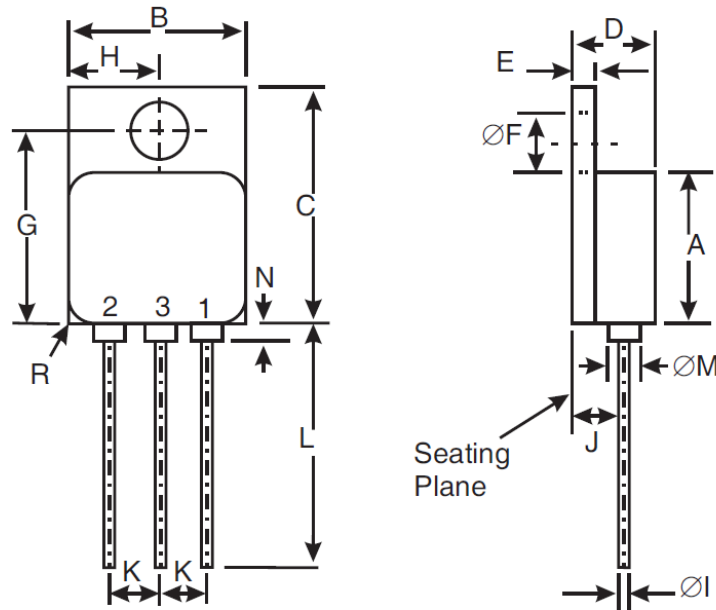
| Symbols | Dimensions mm | | Notes |
|------------------|---------------|-------|-------|
| | Min | Max | |
| $\varnothing a$ | 4.83 | 5.35 | |
| A | 6 | 6.6 | |
| $\varnothing b$ | 0.4 | 0.533 | 2, 3 |
| $\varnothing b2$ | 0.4 | 0.483 | 2, 3 |
| $\varnothing D$ | 8.31 | 9.4 | |
| $\varnothing D1$ | 7.75 | 8.51 | |
| h | 0.229 | 3.18 | |
| j | 0.71 | 0.864 | |
| k | 0.737 | 1.14 | 4 |
| L | 12.7 | 19 | 2 |
| L1 | - | 1.27 | 2, 3 |
| L2 | 6.35 | - | 2, 3 |
| P | 2.54 | - | 5 |
| Q | - | - | 6 |
| α | 45° BSC | | 1, 7 |
| β | 90° BSC | | 1 |

NOTES:

- Terminal identification is specified by reference to the tab position where Lead 1 = emitter, Lead 2 = base and Lead 3 = collector.
- Applies to all leads.
- $\varnothing b2$ applies between L1 and L2. $\varnothing b$ applies between L1 and 12.7mm from the seating plane. Diameter is uncontrolled within L1 and beyond 12.7mm from the seating plane.

4. Measured from the maximum diameter of the actual device.
5. This zone is controlled for automatic handling. The variation in actual diameter within this zone shall not exceed 0.254mm.
6. The details of outline in this zone are optional.
7. Measured from the tab centreline.

1.7.2 Metal Flange Mount Package (TO-257) - 3 lead



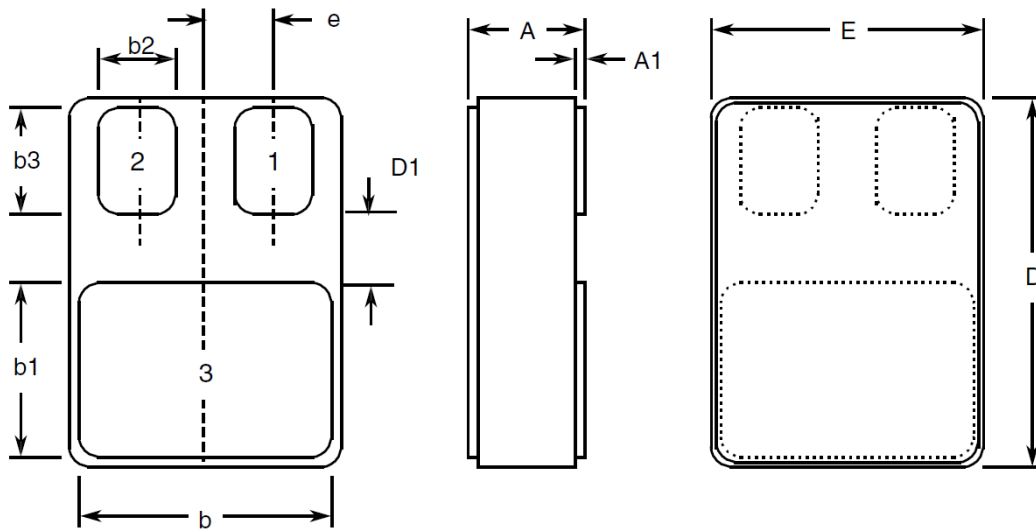
| Symbols | Dimensions mm | | Notes |
|---------|---------------|-------|-------|
| | Min | Max | |
| A | 10.41 | 10.67 | |
| B | 10.41 | 10.67 | |
| C | 16.51 | 16.76 | |
| D | 4.7 | 5.33 | |
| E | 0.89 | 1.14 | |
| ØF | 3.56 | 3.81 | |
| G | 13.39 | 13.64 | |
| H | 5.13 | 5.38 | |
| ØI | 0.64 | 0.89 | 2 |
| J | 2.92 | 3.18 | |
| K | 2.41 | 2.67 | |
| L | 15.24 | 16.51 | |
| ØM | 2.29 Typical | | 2 |
| N | - | 0.71 | 2 |

| Symbols | Dimensions mm | | Notes |
|---------|---------------|-----|-------|
| | Min | Max | |
| R | 1.65 Typical | | 3 |

NOTES:

1. Terminal identification is specified by the components geometry where Lead 1 = emitter, Lead 2 = base and Lead 3 = collector.
2. Applies to all leads.
3. Radius of body corner, 4 places.

1.7.3 Surface Mount Package (SMD.5) - 3 terminal



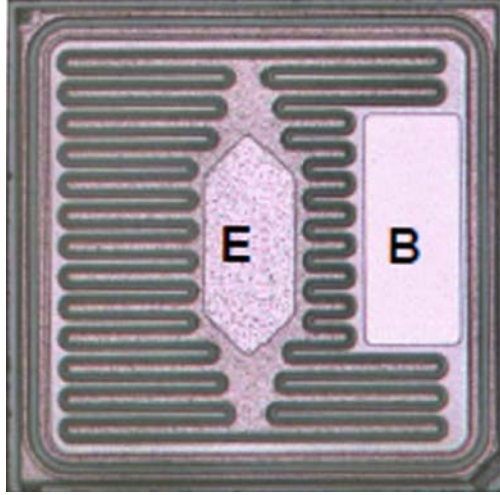
| Symbols | Dimensions mm | | Notes |
|---------|---------------|-------|-------|
| | Min | Max | |
| A | 2.84 | 3.3 | |
| A1 | 0.25 | 0.51 | |
| b | 7.13 | 7.39 | |
| b1 | 5.58 | 5.84 | |
| b2 | 2.28 | 2.54 | 2 |
| b3 | 2.92 | 3.18 | 2 |
| D | 10.03 | 10.28 | |
| D1 | 0.76 | - | 2 |
| E | 7.39 | 7.64 | |
| e | 1.91 BSC | | 2 |

NOTES:

1. Terminal identification is specified by the components geometry where Terminal 1 = emitter (base for Variant 07), Terminal 2 = base (emitter for Variant 07) and Terminal 3 = collector.

2. 2 places.

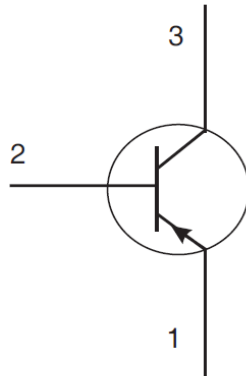
1.7.4 Die



NOTES:

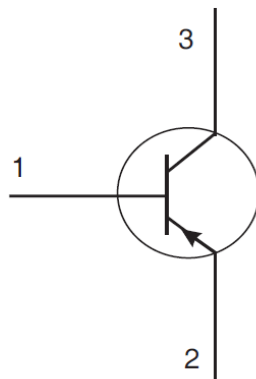
1. Die materials and dimensions:
 - Die substrate: Silicon
 - Die length: 1510 μm
 - Die width: 1500 μm
 - Die thickness: 230 $\pm 20\mu\text{m}$
 - Top Glassivation:
 - P-Vapox with thickness: 720 $\pm 80\text{nm}$ and
 - Nitride with thickness 540 $\pm 60\text{nm}$
 - Top metallisation: Al/Si (1%) with thickness: 2 $\pm 0.2\mu\text{m}$ (Typ.)
 - Backside metallisation: Au/As with thickness: 1.485 $\pm 0.165\mu\text{m}$
 - Emitter pad dimensions: 275 \times 707 μm
 - Base pad dimensions: 300 \times 540 μm
2. Terminal identification: B = Base, E = Emitter
3. Bias details: backside contact = Collector

1.8 FUNCTIONAL DIAGRAM



Variants 01 to 06

- 1. Emitter.
- 2. Base.
- 3. Collector.



Variant 07

- 1. Base.
- 2. Emitter.
- 3. Collector.

NOTES:

1. For TO-39 (Variants 01, 02, 03), the collector is internally connected to the case.
2. For TO-257 (Variants 04, 05), the case is not connected to any lead.
3. For SMD.5 (Variants 06, 07), the lid is not connected to any terminal.
4. For Die Components (Variant 08), the terminal numbering is not applicable.

1.9 MATERIALS AND FINISHES

1.9.1 Materials and Finishes of Packaged Components

For Variants 01 to 07, the materials and finishes shall be as follows:

- (a) Case
 - For the metal can package the case shall be hermetically sealed and have a metal body with hard glass seals.
 - For the metal flange mount package the case shall be hermetically sealed and have a metal body. The leads pass through ceramic eyelets brazed into the frame and the lid shall be welded.
 - For the surface mount package the case shall be hermetically sealed and have a ceramic body with a Kovar lid.
- (b) Leads/Terminals
 - As specified in Para. 1.4.2.

1.9.2 Materials and Finishes of Die Components

For Variant 08, the materials and finishes shall be as specified in Para. 1.7.4.

2 REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

None.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component or its primary package shall be:

- (a) The ESCC qualified components symbol (for ESCC qualified components only).
- (b) The ESCC Component Number (see Para. 1.4.1).
- (c) Traceability information.
- (d) Warning sign for Beryllium Oxide (TO-257 only).

2.3 CASE ISOLATION

For Variants 04 and 05, Case Isolation shall be performed as specified in the ESCC Generic Specification and as follows:

- Test Conditions:
 - Test voltage: 500Vdc
 - Duration of application of test voltage: 1s
 - Points of application of test voltage: between case metal tab and all terminals connected together.
 - Maximum leakage current: 10nA

2.4 TERMINAL STRENGTH

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:

For TO-39, Test Condition: E, lead fatigue.

For TO-257, Test Condition: A, tension, with an applied force of 10N for a duration of 10s.

2.5 VERIFICATION OF SAFE OPERATING AREA

The Safe Operating Area shall be verified as specified in the ESCC Generic Specification and Para. 1.5 Maximum Ratings herein. The test conditions shall be:

Test Method = MIL-STD-750, Method 3051, Continuous DC

$T_{case} = +25^{\circ}C$

$V_{CE} = -18V$

$I_C = -500mA$

Operating Time $\leq 50ms$

2.6 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures.

2.6.1 Room Temperature Electrical Measurements

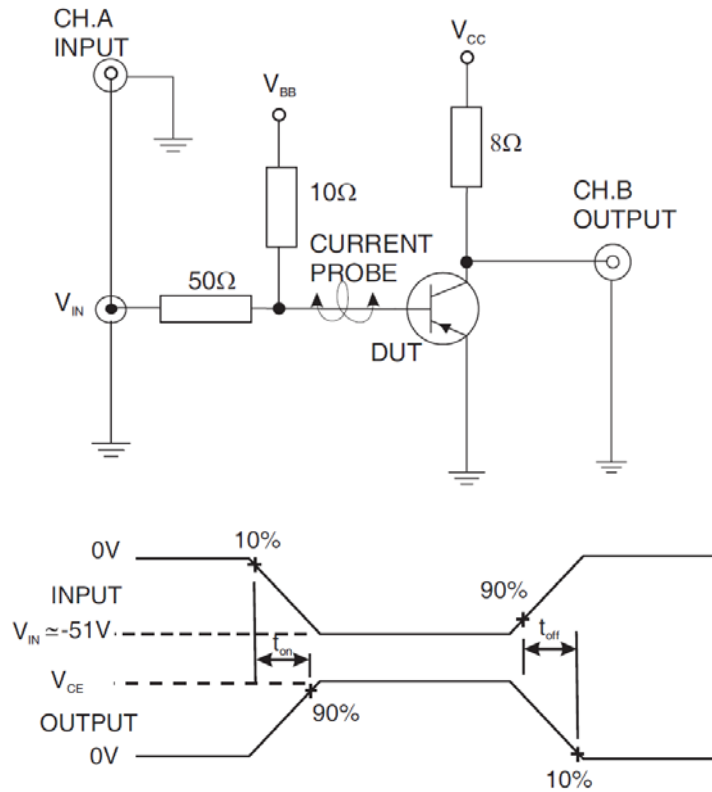
The measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}C$.

| Characteristics | Symbols | MIL-STD-750 Test Method | Test Conditions | Limits | | Units |
|--------------------------------------|---------------|----------------------------|--|--------|------|---------|
| | | | | Min | Max | |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | 3011 | $I_C = -100mA$ Bias condition D Note 1 | -80 | - | V |
| Collector-Emitter Cut-off Current | I_{CES} | 3041 | $V_{CE} = -60V$ Bias condition C | - | -1 | μA |
| | I_{CEO} | 3041 | $V_{CE} = -40V$ Bias condition D | - | -50 | μA |
| Emitter-Base Cut-off Current | I_{EBO1} | 3061 | $V_{EB} = -4V$ Bias condition D | - | -1 | μA |
| | I_{EBO2} | 3061 | $V_{EB} = -5.5V$ Bias condition D | - | -1 | mA |
| Forward-Current Transfer Ratio | h_{FE1} | 3076 | $V_{CE} = -5V$; $I_C = -50mA$ Note 1 | 50 | - | - |
| | h_{FE2} | 3076 | $V_{CE} = -5V$; $I_C = -2.5A$ Note 1 | 70 | 200 | - |
| | h_{FE3} | 3076 | $V_{CE} = -5V$; $I_C = -5A$ Note 1 | 40 | - | - |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | 3071 | $I_C = -5A$ $I_B = -500mA$ Note 1, 2 | - | -1.5 | V |

| Characteristics | Symbols | MIL-STD-750 Test Method | Test Conditions | Limits | | Units |
|--|----------------|----------------------------|--|--------|-------|---------|
| | | | | Min | Max | |
| Base-Emitter Saturation Voltage | $V_{BE(sat)1}$ | 3066 | $I_C = -2.5A$ $I_B = -250mA$ Test condition A Note 1, 2 | - | -1.45 | V |
| | $V_{BE(sat)2}$ | 3066 | $I_C = -5A$ $I_B = -500mA$ Test condition A Note 1, 2 | - | -2.2 | V |
| High Frequency Small Signal Current Gain | h_{fe} | 3306 | $V_{CE} = -5V$, $I_C = -500mA$ $f = 20MHz$ Notes 3, 4 | 3.5 | - | - |
| Output Capacitance | C_{obo} | 3236 | $V_{CB} = -10V$, $I_E = 0A$ $f = 1MHz$ Notes 3, 4 | - | 250 | pF |
| Turn-on Time | t_{on} | - | $I_C = -5A$, $I_{B1} = -500mA$ $I_{B2} = 500mA$ $V_{CC} = -30V$ $V_{BB} = 4V$ $V_{IN} \approx -51V$ Notes 3, 4, 5 | - | 500 | ns |
| Turn-off Time | t_{off} | - | $I_C = -5A$, $I_{B1} = -500mA$ $I_{B2} = 500mA$ $V_{CC} = -30V$ $V_{BB} = 4V$ $V_{IN} \approx -51V$ Notes 3, 4, 5 | - | 1.3 | μs |

NOTES:

1. Pulse measurement: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
2. For TO-39, saturation voltages are measured 6mm from header.
3. For Packaged Components (Variants 01 to 07) all AC characteristics read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
4. For Die Components (Variant 08) all AC characteristics read and record measurements shall be performed on either a sample of 32 components or 100% of the Packaged Test Sublot, whichever is less, with 0 failures allowed
5. t_{on} and t_{off} shall be measured using the following test circuit. The input waveform shall be supplied by a pulse generator with the following characteristics: $t_r \leq 20ns$, Pulse Width = $10\mu s$, Duty Cycle = 1%. The sampling oscilloscope for CH.A and CH.B shall have the characteristics $Z_{IN} \geq 100k\Omega$, $C_{IN} \leq 12pF$ and $t_r \leq 5ns$. Adjustment of V_{IN} shall be made with a suitable current probe to achieve the specified I_{B1} and I_{B2} test conditions, where I_{B1} is the on-state base current and I_{B2} is the post off-state base current.



2.6.2 High and Low Temperatures Electrical Measurements

| Characteristics | Symbols | MIL-STD-750 Test Method | Test Conditions Note 1 | Limits | | Units |
|-------------------------------------|-----------|----------------------------|---|--------|-----|---------|
| | | | | Min | Max | |
| Collector-Base Cut-off Current | I_{CES} | 3041 | $T_{amb} = +150 (+0 -5)^{\circ}C$ $V_{CE} = -60V$, Bias Condition C | - | -10 | μA |
| Forward-Current Transfer Ratio 2 | h_{FE2} | 3076 | $T_{amb} = -55 (+5 -0)^{\circ}C$ $V_{CE} = -5V$ $I_C = -2.5A$ Note 2 | 35 | - | - |

NOTES:

1. Measurements shall be performed on a sample basis as specified in the Generic Specification.
2. Pulsed measurement: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

2.7 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}\text{C}$.

The test methods and test conditions shall be as per the corresponding test defined in Para. 2.6.1, Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

| Characteristics | Symbols | Limits | | | Units |
|--------------------------------------|---------------|----------------------|----------|-------|-------|
| | | Drift Value Δ | Absolute | | |
| | | | Min | Max | |
| Collector-Emitter Cut-off Current | I_{CES} | ± 100 | - | -1000 | nA |
| Forward-Current Transfer Ratio 2 | h_{FE2} | $\pm 25\%$ | 70 | 200 | - |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | ± 100 | - | -1500 | mV |

2.8 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}\text{C}$.

The test methods and test conditions shall be as per the corresponding test defined in Para. 2.6.1, Room Temperature Electrical Measurements.

The limit values for each characteristic shall not be exceeded.

| Characteristics | Symbols | Limits | | Units |
|--------------------------------------|---------------|--------|------|---------------|
| | | Min | Max | |
| Collector-Emitter Cut-off Current | I_{CES} | - | -1 | μA |
| Forward-Current Transfer Ratio 2 | h_{FE2} | 70 | 200 | - |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | - | -1.5 | V |

2.9 HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS

| Characteristics | Symbols | Conditions | Units |
|------------------------|-----------|------------|--------------------|
| Ambient Temperature | T_{amb} | +150 | $^{\circ}\text{C}$ |
| Emitter-Base Voltage | V_{EB} | -4.5 | V |
| Collector-Base Voltage | V_{CB} | -60 | V |
| Duration | t | 48 | hours |

2.10 POWER BURN-IN CONDITIONS

2.10.1 Power Burn-in Conditions (TO-39)

| Characteristics | Symbols | Conditions | Units |
|------------------------|-----------|---|-------|
| Ambient Temperature | T_{amb} | +20 to +50 (1) | °C |
| Power Dissipation | P_{tot} | As per Para. 1.5 Maximum Ratings. Derate P_{tot1} at the chosen T_{amb} using the specified $R_{th(j-a)}$. | W |
| Collector-Base Voltage | V_{CB} | -20 | V |

NOTES:

1. No heat sink nor forced air directly on the device shall be permitted.

2.10.2 Power Burn-in Conditions (TO-257 and SMD.5)

| Characteristics | Symbols | Conditions | Units |
|------------------------|------------|---|-------|
| Case Temperature | T_{case} | +100 (+0 -5) | °C |
| Power Dissipation | P_{tot} | As per Para. 1.5 Maximum Ratings. Derate P_{tot2} at the specified T_{case} using the specified $R_{th(j-c)}$. | W |
| Collector-Base Voltage | V_{CB} | -20 | V |

2.11 OPERATING LIFE CONDITIONS

The conditions shall be as specified in Para. 2.10 Power Burn-in Conditions.

2.12 TOTAL DOSE RADIATION TESTING

All lots shall be irradiated in accordance with ESCC Basic Specification No. [22900](#), low dose rate (window 2: 36 to 360 RAD/h).

2.12.1 Bias Conditions and Total Dose Level for Total dose Radiation Testing

The following bias conditions shall be used for Total Dose Radiation Testing:

| Characteristics | Symbols | Test Conditions | Units |
|--|-----------|---------------------|-------|
| Ambient Temperature | T_{amb} | +20 ±5 | °C |
| Bias Condition 1: Collector-Emitter Voltage | V_{CES} | ≥ 80% $V_{(BR)CEO}$ | V |
| Bias Condition 2: Collector-Emitter Voltage | V_{CES} | 0 | V |

The total dose level applied shall be as specified in Para. 1.4.2 or in the Purchase Order.

2.12.2 Electrical Measurements for Radiation Testing

Prior to irradiation testing the devices shall have successfully met Room Temperature Electrical Measurements specified in Para. 2.6.1.

Unless otherwise stated the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}C$.

Unless otherwise specified the test methods and test conditions shall be as per the corresponding test defined in Para. 2.6.1, Room Temperature Electrical Measurements.

The parameters to be measured during and on completion of irradiation testing are shown below.

| Characteristics | Symbols | MIL-STD-750 Test Method | Test Conditions | Limits | | Units |
|---|----------------|----------------------------|-----------------------------|--------|-------|---------|
| | | | | Min | Max | |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | See Para. 2.6.1 | See Para. 2.6.1 | -80 | - | V |
| Collector-Emitter Cut-off Current | I_{CES} | See Para. 2.6.1 | See Para. 2.6.1 | - | -1 | μA |
| | I_{CEO} | See Para. 2.6.1 | See Para. 2.6.1 | - | -50 | μA |
| Emitter – Base Cutoff Current | I_{EBO1} | See Para. 2.6.1 | See Para. 2.6.1 | - | -1 | μA |
| | I_{EBO2} | See Para. 2.6.1 | See Para. 2.6.1 | - | -1 | mA |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | See Para. 2.6.1 | See Para. 2.6.1 | - | -1.5 | V |
| Base-Emitter Saturation Voltage | $V_{BE(sat)1}$ | See Para. 2.6.1 | See Para. 2.6.1 | - | -1.45 | V |
| | $V_{BE(sat)2}$ | See Para. 2.6.1 | See Para. 2.6.1 | - | -2.2 | V |
| Forward-Current Transfer Ratio (post irradiation gain calculation) (Note 1) | $[h_{FE1}]$ | 3076 | $V_{CE} = -5V, I_C = -50mA$ | [25] | - | - |
| | $[h_{FE2}]$ | | $V_{CE} = -5V, I_C = -2.5A$ | [35] | 200 | - |
| | $[h_{FE3}]$ | | $V_{CE} = -5V, I_C = -5A$ | [20] | - | - |

NOTES:

1. The post-irradiation gain calculation of $[h_{FE}]$, made using h_{FE} measurements from prior to and on completion of irradiation testing and after each annealing step if any, shall be as specified in MIL-STD-750 Method 1019.

APPENDIX 'A'
AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

| ITEMS AFFECTED | DESCRIPTION OF DEVIATIONS |
|---|---|
| Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures | For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications shall be used instead of the following ESCC Basic Specifications: <ul style="list-style-type: none"> • No. 20400, Internal Visual Inspection: replaced by MIL-STD-750 Test Method 2072. • No. 20500, External Visual Inspection: replaced by MIL-STD-750 Test Method 2071. • No. 20900, Radiographic Inspection of Electronic Components: replaced by MIL-STD-750 Test Method 2076. |
| Para. 2.1.1, Deviations from the Generic Specification: Screening Tests - Chart F3 | Solderability is not applicable unless specifically stipulated in the Purchase Order. |
| Para. 2.6.1, Room Temperature Electrical Measurements | All AC characteristics (Para. 2.6.1, Notes 3 and 4) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order. |
| Para. 2.6.2, High and Low Temperatures Electrical Measurements | All characteristics specified may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes characteristic measurements at high and low temperatures per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order. |
| Para. 2.10.2, Power Burn-in Conditions | For TO-257 and SMD.5 packaged Variants (Variants 04 to 07), the following alternate Power Burn-in conditions may be applied: <ul style="list-style-type: none"> – Ambient Temperature (T_{amb}): +20 to +50°C (Note 1) – Power Dissipation (P_{tot}): As per Para. 1.5 Maximum Ratings. Derate P_{tot1} at the chosen T_{amb} using the specified $R_{th(j-a)}$ (W) – Collector-Base Voltage (VCB): 20 to 40V – Note 1: No heat sink nor forced air directly on the device shall be permitted. |